



650v 1.5 Ω N-Channel Power Mosfet

CMX09165NH-252

Data Sheet

Version: V0.1

Features

- Originative New Design
- Superior Avalanche Rugged Technology
- Robust Gate Oxide Technology
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge : 22nC (Typ.)
- Extended Safe Operating Area

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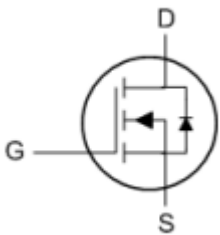
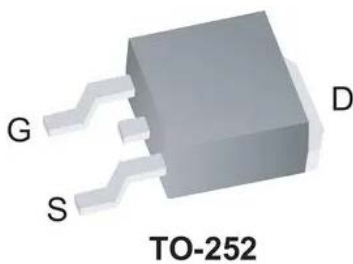
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1 Description

The CMX09165NH-252 uses advanced MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality.

Can be used in switching mode power supply, motor drive, charger / power supply / UPS, LED display/ environment lighting, appliances and white goods.

2 Pin Configuration



3 Absolute Ratings ($T_A = 25^\circ\text{C}$ in a TO-252 package unless otherwise noted)

Parameter	Symbol	Value		Units
Drain-Source Voltage	V_{DS}	+650		V
Gate-Source Voltage	V_{GS}	± 30		V
Junction Temperature Maximum	T_{JMAX}	150		$^\circ\text{C}$
Storage Temperature	$T_{Storage}$	-55 to 150		$^\circ\text{C}$

4 Thermal Characteristics

Parameter	Symbol	Value	Units
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	50	$^{\circ}\text{C}/\text{W}$

5 Electrical Characteristics

Static ($T_J=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	650	---	---	V
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	---	---	± 500	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	---	---	1	μA
		$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}, T_J = 125^{\circ}\text{C}$	---	---	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 1.5\text{A}$	---	1.5	1.9	Ω
		$V_{GS} = 8\text{V}, I_D = 1.5\text{A}$	---	1.8	---	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.4	3	3.6	V
Diode Forward Voltage	V_{SD}	$I_S = 7.2\text{A}, V_{GS} = 0\text{V}$	---	---	1.4	V
Continuous Source Current	I_S	$V_{GS} = 0\text{V}, V_{DS} \text{Open}, f=1\text{MHz}$	---	---	7	A
Dynamic ($T_J=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 400\text{V},$ $f = 250\text{kHz}$	---	208	---	pF
Output Capacitance	C_{oss}		---	10.8	---	
Reverse Transfer Capacitance	C_{rss}		---	3.6	---	
Total Gate Charge	Q_g	$V_{DS} = 520\text{V}, I_D = 7.2\text{A},$ $V_{GS} = 10\text{V}$	---	22	---	nC
Gate-Source Charge	Q_{gs}		---	5	---	
Gate-Drain Charge	Q_{gd}		---	9	---	
Turn-on delay time	$T_{d(on)}$	$V_{DS} = 325\text{V}, I_D = 7.2\text{A},$ $R_G=25\Omega$	---	17	---	nS
Rise time	T_r		---	61	---	
Turn-off delay time	$T_{d(off)}$		---	81	---	
Fall time	T_f		---	65	---	

6 Typical Characteristics

Typical Electrical Characteristics

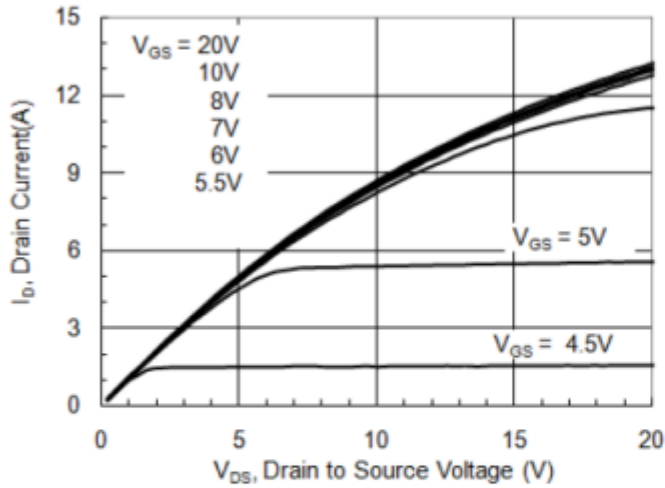


Fig1. Output characteristics

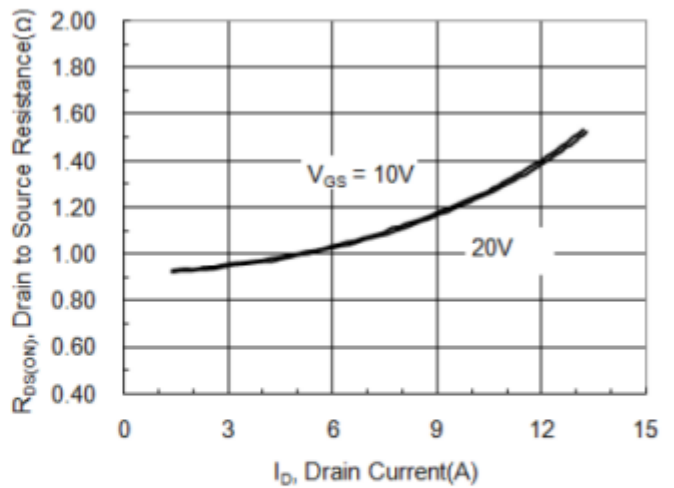


Fig2. Drain-source on-state resistance

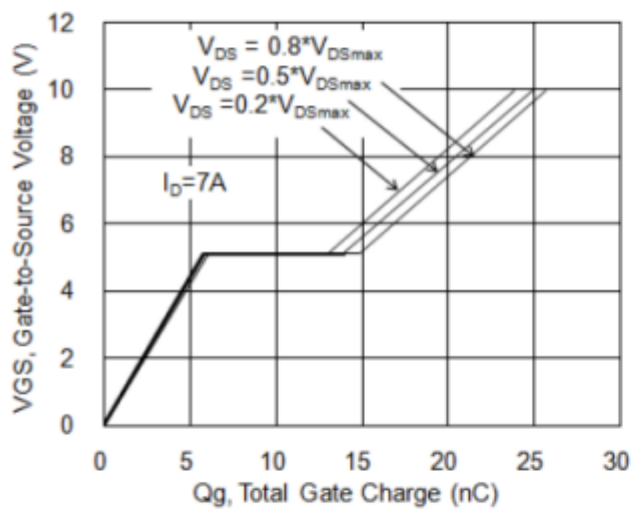


Fig3. Gate charge characteristics

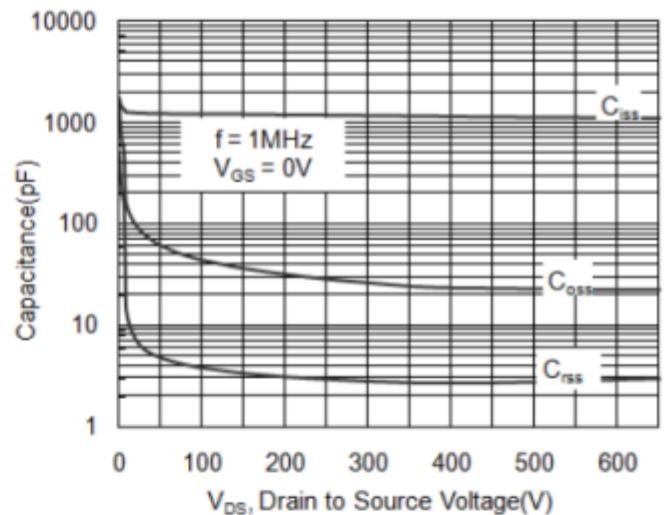
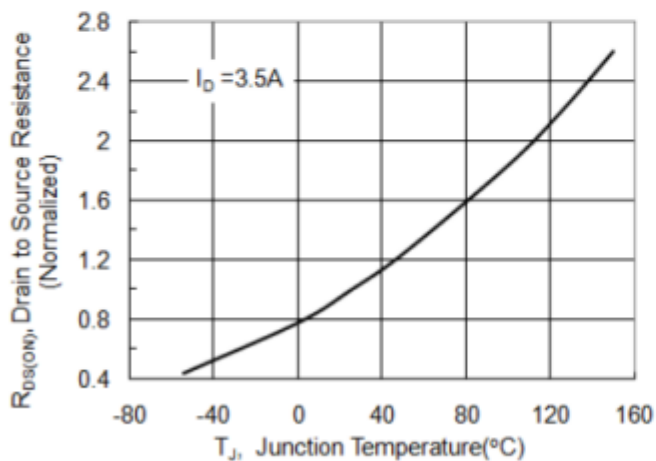
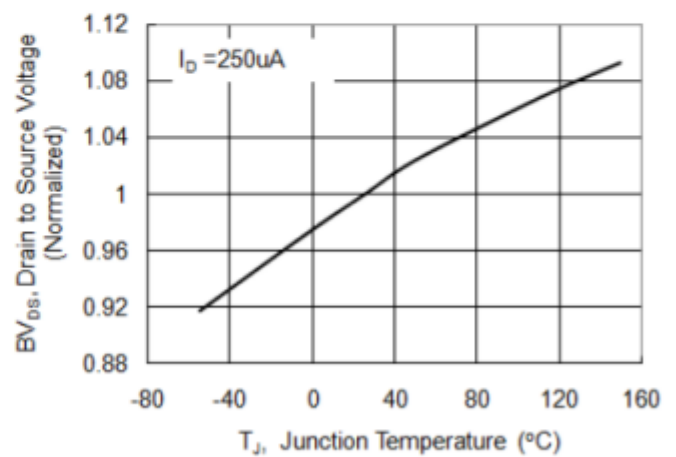


Fig 4. Capacitance Characteristics

Fig 5. $R_{DS(ON)}$ vs junction temperatureFig 6. BV_{DS} vs junction temperature

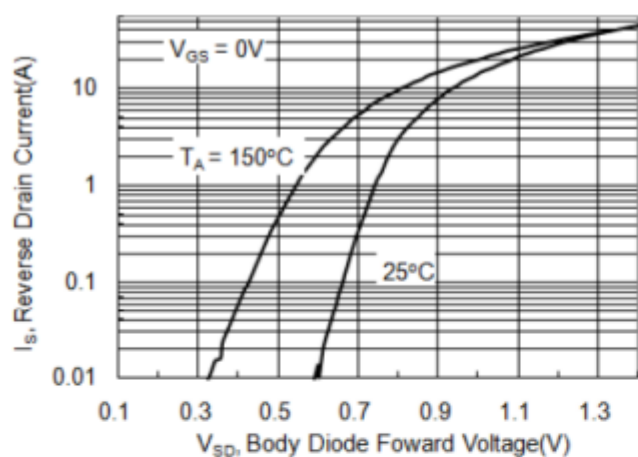


Fig 7. Forward characteristics of reverse diode

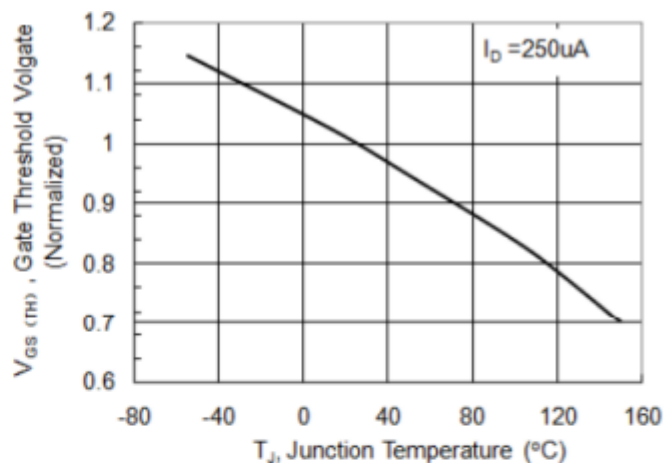


Fig 8. $V_{GS (TH)}$ vs junction temperature

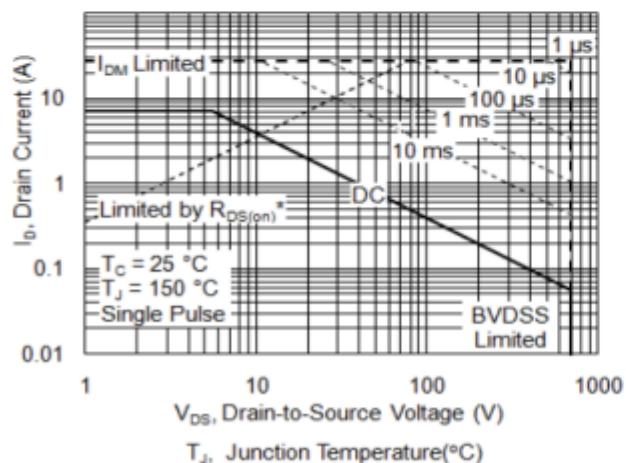
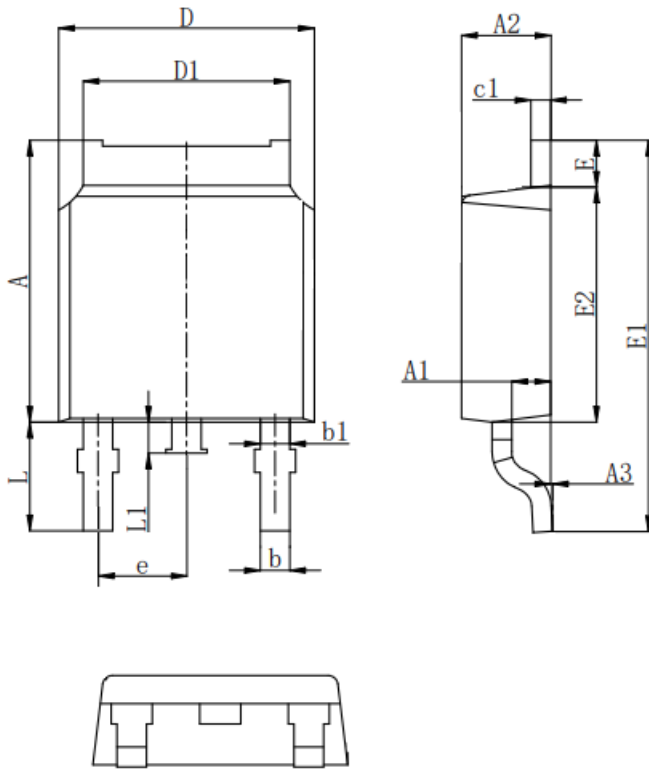


Fig 9 . Safe operating area

7 Package Outlines

TO-252



Dimension	A	A1	A2	A3	b	b1	c1	D	D1	E	E1	E2	e	L	L1
Min.	7.05	0.96	2.25	0				6.55	5.22	0.95	9.7	6.05		2.65	0.7
Typ.	7.1	1.01	2.3	0.05	0.76	1	0.508	6.6	5.32	1	9.9	6.1	2.286	2.8	0.8
Max.	7.15	1.06	2.35	0.1				6.65	5.42	1.05	10.1	6.15		2.95	0.9